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APPLICATION
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TITLE: MAGNETIC FIELD EFFECT TRANSISTOR,
 LATCH AND METHOD

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MAGNETIC FIELD EFFECT TRANSISTOR, LATCH AND METHOD

FIELD OF THE INVENTION

[0001] The present invention relates generally to magnetic field detection, and more particularly to a magnetic field effect transistor, latch and methods.

BACKGROUND OF THE INVENTION

[0002] Many electronic applications require the detection of a magnetic field. Dual drain magnetic field effect transistors (MAGFETs) are known, and are very effective for determining the strength of a magnetic field. In some cases, MAGFETs are also used to detect the absence and presence of a magnetic field. However, because of the sensitivity of a conventional MAGFET there is a limit on the smallest detectable magnetic field.

[0003] Although the sensitivity of the MAGFET can be increased by introducing multiple gates to generate a longitudinal potential gradient along the channel, as for example detailed in F. J. Kub and S. S. Scott, Multiple-gate split-drain MOSFET magnetic-field sensing device and amplifier, *IEDM Technical Digest*, IEEE, New York, 1992, pp. 517-520, such modifications typically lead to substrate bias. Furthermore, due to velocity saturation, the improvement of the sensitivity by this approach is limited.

[0004] Accordingly, there is a need for a more sensitive magnetic field detector and method.

SUMMARY OF THE INVENTION

[0005] A split drain MAGFET includes at least one supplemental gate to exert a lateral electrical field in the channel of the MAGFET... Connection of the supplemental gate in feedback with one of the two drain contacts allows the MAGFET to act as a latch sensitive to the presence of an external magnetic field. Preferably, the MAGFET includes two laterally spaced supplemental gates, allowing for the detection of an external magnetic field and its orientation.

[0006] In accordance with an aspect of the present invention, there is provided a field effect transistor for detecting a magnetic field... The field effect transistor includes a doped layer; doped source and drain regions formed in the doped layer; first and second drain contacts spaced laterally relative to the length of the channel interconnected with the drain region... The doped layer defines a lengthwise extending channel between the source and drain regions. A gate proximate the channel controls current that may flow from the source to the drain region... Additional first and second supplemental gates are spaced laterally relative to the length of the channel... The first and second supplemental gates are electrically isolated from each other and the gate. Thus, a potential difference between the first and second supplemental gates exerts a lateral electric field in the channel.

[0007] In accordance with another aspect of the present invention, there is provided a method of detecting a magnetic field in a split drain field effect transistor including a source region, a channel interconnecting the source region to a drain region, and first and second drain contacts for guiding current from laterally spaced portions of the channel... The method includes applying a controlled electric field laterally across the channel in a direction parallel to the force experienced by electrons in the channel under the influence of a magnetic field.

[0008] In accordance with yet another aspect of the present invention, a field effect transistor includes a semiconductor substrate; a source region and a drain

region; a channel formed in the substrate for guiding current from the source region to the drain region along a lengthwise extent of the channel; a gate in proximity with the channel for controlling current from the source to the drain. The drain region includes first and second drain contacts, each of which guides current from a lateral portion of the channel. The first and second supplemental gates are proximate the channel for establishing an electric field in the channel, in a direction perpendicular to the lengthwise extent.

[0009] Transistors exemplary of embodiments of the present invention may be interconnected to act as magnetic latches, whose state is controlled by the presence of a magnetic field. Such latches may be used as switches or memory elements.

[0010] Other aspects and features of the present invention will become apparent to those of ordinary skill in the art upon review of the following description of specific embodiments of the invention in conjunction with the accompanying figures.

BRIEF DESCRIPTION OF THE DRAWINGS

[0011] In the figures which illustrate by way of example only, embodiments of the present invention,

[0012] **FIG. 1** is a perspective cross-sectional view of a conventional MAGFET;

[0013] **FIG. 2** is a perspective cross-sectional view of a MAGFET, exemplary of an embodiment of the present invention;

[0014] **FIG. 3** is a partially exploded view of the MAGFET of **FIG. 2**;

[0015] **FIG. 4** is a top plan view of the MAGFET of **FIG. 2** interconnected as a latch;

[0016] FIG. 5 is a schematic symbol of the MAGFET of FIG. 2 interconnected as a latch;

[0017] FIG. 6 is a diagram illustrating drain voltage of the magnetic field effect transistor of FIG. 2 in the presence of a magnetic field; and

[0018] FIG. 7 is a schematic diagram of a device for detecting a magnetic field including the MAGFET of FIG. 2.

DETAILED DESCRIPTION

[0019] FIG. 1 illustrates a convention n-channel split drain magnetic field effect transistor ("MAGFET") 100. As illustrated, MAGFET 100 includes a p-type semiconductor layer 104 configured as a well within a semiconductor substrate 102. Formed within layer 104 are n-type source and drain regions 106 and 108. The p-type semiconductor layer 104 extending between source and drain regions 106 and 108 defines a lengthwise extending channel 110. A conductive gate 112 is formed above channel 110. A metal contact 114 is formed atop source 106. Two laterally conductive contacts 116a and 116b are formed above drain region 108. As illustrated, contacts 116a and 116b are spaced laterally along the width of channel 110.

[0020] As will be appreciated substrate 102 could be eliminated and layer 104 could act as a p-type substrate for a suitable MAGFET.

[0021] Now, in the absence of an external magnetic field, MAGFET 100 functions in much the same way as a conventional field effect transistor. A voltage applied to gate 102 modulates the depth of channel 110 and thereby controls the amount of current that may flow between source region 106 and drain region 108, I_{SD} . Current through drain region 106, is split evenly between contacts 116a and 116b with $.5I_{SD} = I_{Da} = I_{Db}$ flowing through each of contacts

116a and 116b.

[0022] In the presence of a magnetic field, electrons passing between source and drain along a lengthwise extent of channel **110** experience a Lorentz force perpendicular to the direction of travel of the electrons and the magnetic field... If the magnetic field includes a component perpendicular to the width and length of channel **110** (i.e. in the vertical direction), current along the length of channel **110** is laterally redistributed, with more current flowing in one lateral half of the channel than the other... The resulting current, through drains contacts **116a** and **116b** may be expressed as $I_{Da} = .5(I_{SD} + i)$ for contact **116a**, and $I_{Db} = .5(I_{SD} - i)$ for contact **116b**... The magnitude of the difference between I_{Da} and I_{Db} is attributable to the external magnetic field and may be used to assess the magnitude of the external magnetic field... Several variations to the basic MAGFET structure are known... Example MAGFETs are more particularly detailed in Henry P. Baltes and Radivoje S. Popovic, Integrated Semiconductor Magnetic Field Sensors, Proceedings of IEEE, vol. 74, pp. 1107-1132, 1986.

[0023] **FIGS. 2-4** illustrate a MAGFET **200**, exemplary of an embodiment of the present invention... MAGFET **200** may be fabricated using conventional CMOS fabrication techniques, allowing formation of CMOS with double conductive layers... Again, MAGFET **200** includes a p-type semi-conductor layer **204** that may be formed as on an n-type semi-conductor substrate **202**. Alternatively, MAGFET **200** could be formed directly on layer **204** acting as a substrate... Formed within layer **204** are n-type source and drain regions **206** and **208**... Channel **210** extends lengthwise between source and drain **206** and **208**. Conductive gate **212** is formed above channel **210**... Two additional supplemental gates **220a** and **220b** are formed above channel **210** in overlapping relationship with gate **212**... The two supplemental gates **220a** and **220b** are electrically isolated from each other and gate **212**... In the exemplary MAGFET **200**, supplemental gates **220a** and **220b** are formed in a poly-silicon layer underlying the poly-silicon layer of the conventional gate **212**... Again, conductive contact **214** is formed atop source **206**... Two laterally spaced conductive contacts **216a**

and **216b** are formed atop drain region **208**.

[0024] Supplemental gates **220a** and **220b**, like contacts **216a** and **216b**, are spaced along the width of channel **210**. Supplemental gate **220a** and contact **216a** are formed proximate the rear lateral half of channel **210**. Supplemental gate **220b** and contact **216b** are formed proximate the front lateral half of channel **210**. For ease of illustration, **FIG. 4** illustrates the MAGFET **200** in top plan view, with supplemental gates **220a** and **220b** shown in phantom. In the absence of an external magnetic field, a voltage applied to gate **212** modulates the depth of channel **210** and thereby controls the amount of current that may flow between source region **206** and drain region **208**, I_{SD} . Additional gates **220a** and **220b** serve much the same purpose as gate **212**. However, as these supplemental gates **220a** and **220b** only extend over a portion of the width of channel **210**, each one only modulates the depth of a width-wise extending portion/region of the channel. That is, a voltage applied to supplemental gate **220b** modulates the depth of the front portion of the width of channel **210**. Similarly, a voltage applied to supplemental gate **220a** modulates the depth of the rear portion of the width of channel **210**. With a potential difference between gates **220a** and **220b** a width-wise lateral electric field is produced in channel **210**.

[0025] As such, again, in the absence of a magnetic field, the amount of current flowing between source region **206** and drain region **208** may be controlled by the potentials applied to gate **212**, **220a**, and **220b**. Currents through drain region **208** will only be split evenly between contacts **216a** and **216b** if the potential applied to supplemental gates **220a** and **220b** are equal. When a voltage is applied across the two supplemental gates **220a** and **220b**, a potential will be developed beneath the respective gates and a lateral electric field will be formed in channel **210**.

[0026] As a consequence the distribution of source to drain current exiting each drain contact **216a** and **216b** may be controlled by the potential difference

between supplemental gates **220a** and **220b**.

[0027] Now, in order to provide a magnetic sensor that is highly sensitive to an external magnetic field in the vertical direction, MAGFET **200** may be connected as a latch by connecting gates **220a** and **220b** in feedback to drain contacts **216a** and **216b**, as illustrated in **FIG. 4**. Under a load (which may be passive, active or even a p-channel MAGFET counterpart) the current imbalance in the two drain contacts **216a** and **216b** also results in a voltage difference across the two drain contacts **216a** and **216b** and across the two supplemental gates **220a** and **220b**. Specifically, the current imbalance through contacts **216a** and **216b** applies a controlled electric field, laterally across the channel in a direction parallel to the Lorentz force experienced by electrons in the channel under the influence of a magnetic field. As a result, the state of MAGFET **200** connected as a latch is determined by the applied magnetic field.

[0028] Because the rear drain contact **216a** is interconnected with the front supplemental gate **220b**, and the front drain contact **216b** is interconnected with rear supplemental gate **220a**, any imbalance in current through contact **216a** or **216b** will effectively be amplified: more current through contact **216a** exerts a voltage on the supplemental gate controlling the lateral potential of that portion of the channel **210** associated with drain contact **216b**, and generating a lateral field toward the portion of the channel associated with contact **216a**, causing a further increase in current through contact **216a**. The positive feedback repeats until the voltage difference between the two drain contacts **216a** and **216b** reaches the positive or negative maximum value allowed by the circuit construction.

[0029] Conveniently, then, MAGFET **200** acts as a latch, magnifying any current imbalance between drain contact **216a** and **216b**. Thus, even in the presence of a small magnetic field having a component direction perpendicular (i.e., along the depth of) channel **210**, a large current imbalance between contacts **216a** and **216b** will be produced, allowing MAGFET **200** to be used to detect minute magnetic fields, having a component in the vertical direction. The

latch, however, has only two equilibrium states... Owing to the positive feedback, the latch is highly sensitive to the presence and orientation of a magnetic field, and thus, can be used to recognize the magnetic field pattern with the two polarities.

[0030] Optionally, once MAGFET **200** is latched, the latch may be reset, as detailed below.

[0031] **FIG. 5** schematically illustrates the MAGFET **200** of **FIG. 2**, using a schematic symbol **230**. As illustrated, schematic symbol **230** is formed from the schematic symbol for a conventional MAGFET (such as MAGFET **100** of **FIG. 1**), but modified slightly to illustrate the supplemental gates **220a** and **220b**, and their feedback interconnection to drain contacts **216b** and **216a**.

[0032] **FIG. 7** illustrates a device including MAGFET **200** and a suitable clock circuit that may be used to reset a latched MAGFET **200** (as depicted using symbol **230**) by temporarily shorting supplemental gates **220a** and **220b** by switch **232**.

[0033] The magnetic response of an example MAGFET **200** with drain contacts **216a** and **216b** loaded with a pair of p channel MOSFETS is depicted in **FIG. 6**. In the depicted arrangement, when the magnetic field is crosses a threshold of about .5mT MAGFET **200** transitions between high and low voltage levels. However, this threshold is dependent on the particular geometry, interconnection, etc. of MAGFET **200**. When the sensor is exposed under the magnetic field strength at the turning point ($B = 0$ for offset = 0) the output state is arbitrary.

[0034] As will now be appreciated, supplemental gates **220a** and **220b** could be internally cross-connected in MAGFET **200** to form a latch or alternatively externally cross-connected. The response and sensitivity of a latch including MAGFET **200** could be controlled by interposing an amplifier between the two supplemental gates by amplifying the forward feedback effect. Also, the shape of

the hysteresis can be modified by the aspect ratio of the channel and gate (i.e., the width/length of the channel **210**, the dimension of the supplemental gates **220a**, **220b**), the load of the latch (resistor, p-channel MOSFET pair etc.) and other parameters in the circuit configuration (using the magnetic latch to form any functional circuit) to suit particular applications. The turning point (the switching B field) can similarly be adjusted by the above parameters to cater a switching function.

[0035] Similarly, although an n-channel MAGFET **200** has been illustrated, MAGFET **200** could easily be formed as a p-channel MAGFET.

[0036] As a further alternative, supplemental gates **220a** and **220b** could be located vertically above gate **212**. The resulting MAGFET may be slightly less sensitive as the voltage at the gate layer farther from the channel **210**, attributable to the magnetic field, will exert a lesser lateral field in the channel.

[0037] As will now be appreciated, supplemental gates **220a** and **220b** need only be suitably arranged relative to each other and in proximity to channel **210**. Thus MAGFET **200** could be modified to include supplemental gates beneath channel **210**, at the sides of channel **210** or elsewhere.

[0038] A person of ordinary skill, will now appreciate numerous applications for MAGFET **200** configured as a magnetic latch. Such a magnetic latch may, for example, be configured as a transistor switch. Gate **220** may be biased so that channel **210** conducts. In such a configuration, source to drain current through one of drain contacts **216a** and **216b** will be switched on allowing control of another electronic circuit. Similarly, such a magnetic latch may be used as a magnetic memory element. States of the memory element may be altered through an external magnetic field, and sensed electrically at one of drain contacts **216a** and **216b**. Multiple latches may be configured as a memory bank, with each latch storing a unit of binary information.

[0039] Of course, the above described embodiments are intended to be

illustrative only and in no way limiting... The described embodiments of carrying out the invention are susceptible to many modifications of form, arrangement of parts, details and order of operation... The invention, rather, is intended to encompass all such modification within its scope, as defined by the claims.